

H

44. The semiconductor structure of claim 39, further comprising:
a metal layer disposed on the substrate; and
wherein the first layer of spin-on glass is disposed on the metal layer.

45. The semiconductor structure of claim 39, further comprising:
a metal layer disposed on the substrate;
a second dielectric disposed on the metal layer; and
wherein the first layer of spin-on glass is disposed on the second dielectric.

46. The semiconductor structure of claim 39 wherein the first dielectric
comprises a low-temperature oxide.

47. The semiconductor structure of claim 39, further comprising a planarized
boundary that includes the planarized second layer of spin-on glass and a planarized
portion of the first dielectric.

48. The semiconductor structure of claim 39, further comprising a planarized
boundary that includes the planarized second layer of spin-on glass, a planarized
portion of the first dielectric, and a planarized portion of the first layer of spin-on glass.

REMARKS

Claims 1 – 48 are pending in this broadening reissue application.

The Applicants have added new claims 23 - 48 to broaden the scope of protection to their invention.

The Applicants have added no new matter to the reissue application.

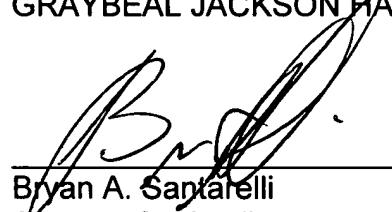
In light of the foregoing, original claims 1 – 22 and new claims 23 – 48 are in condition for full allowance, and that action is respectfully requested.

If the Examiner believes that a telephone interview would be helpful, he is respectfully requested to contact the Applicants' attorney, Bryan Santarelli, at (425) 455-5575.

DATED this 16th day of November, 2001.

Respectfully submitted,

GRAYBEAL JACKSON HALEY LLP



Bryan A. Santarelli
Attorney for Applicants
Registration No. 37,560
155-108th Avenue N.E., Ste 350
Bellevue, WA 98004-5901
(425) 455-5575

DEPARTMENT OF COMMERCE
U.S. PATENT AND TRADEMARK OFFICE